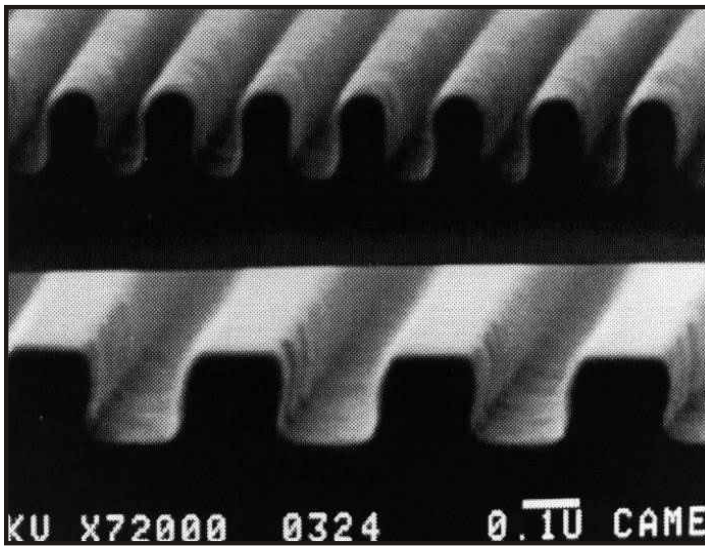
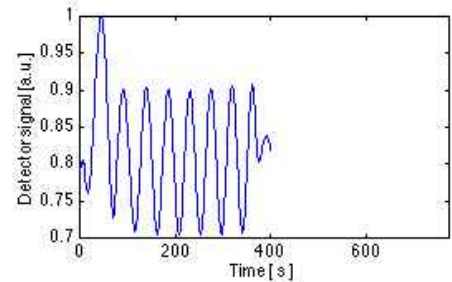
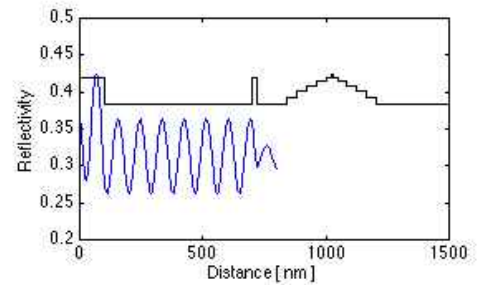


Ionfab Data

InGaAs/AlGaAs RIBE - CAIBE using laser interferometry



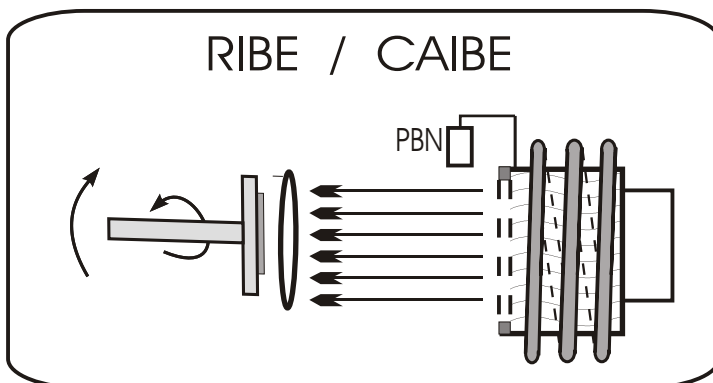
Courtesy of Chalmers University
Photonics Laboratory
Niklas Eriksson, Anders Larsson, Mats Hagberg



Ionfab 300 Plus

In-situ monitoring using a HeNe laser interferometer

The upper figure shows the waveguide structure and the calculated reflectivity. The lower figure shows the detector signal during etching. The material is an InGaAs/AlGaAs laser structure with an etch-stop layer incorporated in the upper cladding layer, a Cl/BCl₃-based RIBE process was used here.



Technology:

- Etch Mode: RIBE + CAIBE
- BCl₃/ Cl₂ -processes
- Rotating substrate with adjustable tilt
- Ion source: 15 cm, 13.56 MHz driven
- Ion Optics: high uniformity
- Beam Neutralisation: filamentfree PBN